

AMENDMENT

In the Claims:

This listing of claims will replace all prior versions, and listings of claims in the application:

Listing of Claims:

1-19. (Canceled)

20. (currently amended) Structure for vertical electrical conduction comprising a thin layer (2) integral with a support of conductive or semi-conductive material, the thin layer (2) being a layer of conductive or semi-conductive material made insulating by ion implantation except for at least one zone (9) that allows a vertical electrical connection ~~through the entire thickness of the thin layer (2) electrically connecting the support to a face of the thin layer opposite to the support, wherein said layer (2) and at least one zone (2) substantially have the same thickness~~ between the face of the thin layer opposite to the support and the face of the support opposite to the thin layer.

21. (currently amended) Structure according to Claim 20, ~~characterized in that the~~ wherein said thin layer comprises a multitude of said zones, said multitude of zones being distributed over the entire surface of the thin layer.

22. (currently amended) Structure according to Claim 20, ~~characterized in that the~~
wherein said thin layer comprises one of said zone or a plurality of said zones
concentrated to constitute at least one conductive path or at least one conductive track.

23. (currently amended) Structure according to claim 20, ~~characterized in that the~~
wherein said thin layer (2) is made integral with the support (3) through an intermediate
conductive interface.

24. (currently amended) Structure according to Claim 23, ~~characterized in that~~
wherein said intermediate conductive interface ~~is constituted by~~ comprises a metal layer.

25. (currently amended) Structure according to Claim 24, ~~characterized in that~~
wherein said metal layer is a layer of palladium.

26. (currently amended) Structure according to claim 23, ~~characterized in that~~
wherein a deposition of conductive bonding materials is associated with said intermediate
conductive interface.

27. (currently amended) Structure according to Claim 26, ~~characterized in that the~~
wherein said conductive bonding materials are successive deposits of titanium, nickel and
gold.

28. (currently amended) Structure according to claim 20, ~~characterized in that the~~
wherein said thin layer (2) is made integral with the support (3) through the use of a
brazing material.

29. (currently amended) Structure according to Claim 28, ~~characterized in that the~~
wherein said brazing material is based on indium.

30. (currently amended) Structure according to claim 20, ~~characterized in that~~
wherein the material of the thin layer (2) is chosen from among SiC, GaAs and InP.

31. (currently amended) Structure according to claim 23, ~~characterized in that the~~
wherein said support (3) is made of silicon.

32. (currently amended) Structure according to claim 22, ~~characterized in that the~~
wherein said thin layer (2) is made integral with the support (3) through an intermediate
conductive interface.

33. (currently amended) Structure according to claim 25, ~~characterized in that~~
wherein a deposition of conductive bonding materials is associated with said metal layer.

34. (currently amended) Structure according to claim 22, characterized in that ~~the~~
said thin layer (2) is made integral with the support (3) through the use of a brazing
material.

35. (currently amended) Structure according to claim 29, ~~characterized in that~~
wherein the material of the thin layer (2) is chosen from among SiC, GaAs and InP.

36. (currently amended) Structure according to claim 29, ~~characterized in that the~~
wherein said support (3) is made of silicon.